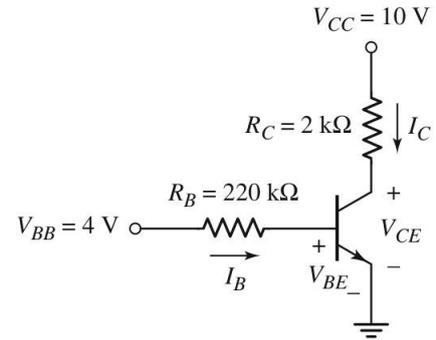


國立高雄海洋科技大學 106 學年度碩博士班考試入學
微電子工程系碩士班---微電子學試題【*須使用計算機】

1.10% Figure (a) shows the circuit without explicitly showing the voltage sources. The parameters are: $V_{BB}=4\text{ V}$, $R_B=220\text{ k}\Omega$, $R_C=2\text{ k}\Omega$, $V_{CC}=10\text{ V}$, $V_{BE(\text{on})}=0.7\text{ V}$, and $\beta=200$.

- (1) Calculate the base (I_B), collector (I_C), and emitter currents (I_E) and the C-E voltage (V_{CE}) for a common-emitter circuit.
- (2) Calculate the transistor power dissipation (P_T).

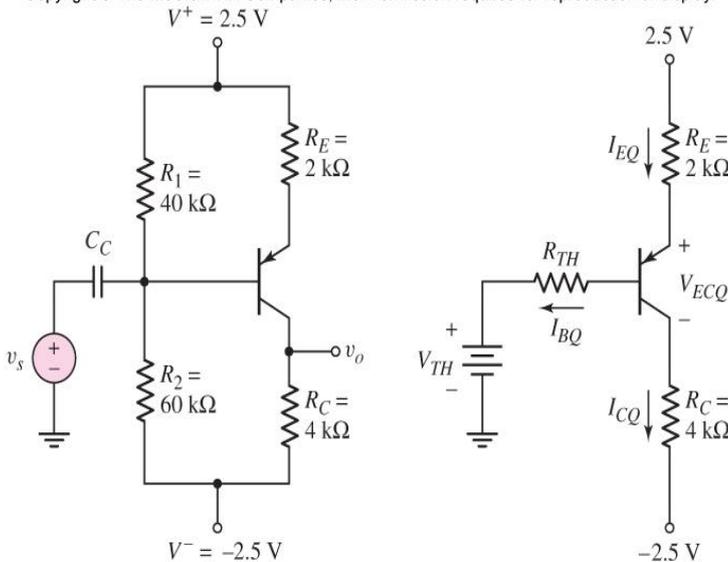


(a)

2.14% Analyze a pnp transistor circuit. Consider the circuit shown in Figures (a) and (b). The transistor parameters are $V_{EB(\text{on})}=0.7\text{ V}$, $\beta=80$, and $V_A=\infty$. Determine the quiescent parameter values and then the small-signal voltage gain including: (Hint: $r_\pi = \frac{\beta V_T}{I_{CQ}}$ and $V_T=0.026\text{ V}$)

- (1) Thevenin equivalent voltage (V_{TH}),
- (2) Thevenin equivalent resistance (R_{TH}),
- (3) collector current (I_{CQ}),
- (4) collector-emitter voltage (V_{ECQ}),
- (5) diffusion resistance (r_π),
- (6) transconductance (g_m),
- (7) small-signal transistor output resistance (r_o).

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(a)

(b)

背面有試題

3. 16% (a) What are the two basic processes which cause electrons and holes to move in a semiconductor? 4% (b) Describes and plots how the effect on e^- in (a) caused by electric field contribute to the current? 3% (c) Describes and plots how the effect on e^- in the other process of (a) contribute to the current? 3% (d) Describes and plots how the effect on h^+ in (a) caused by electric field contribute to the current? 3% (e) Describes and plots how the effect on h^+ in the other process of (a) contribute to the current? 3%

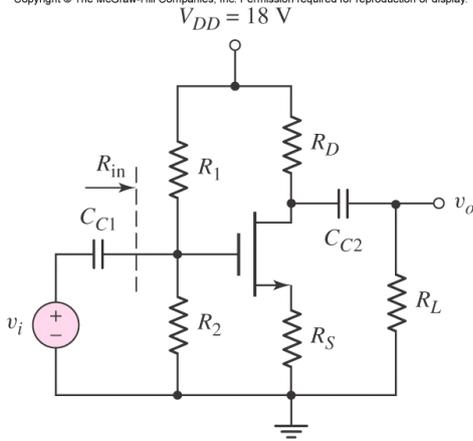
All the answers of (b) to (e) have to be included vector and moving direction.

$$J_{np} = |q| \times n(p) \times |v_{dn}| = |q| \times n(p) \times |\mu_{np} E|$$

$$J_{np} = |q| D_{np} \frac{dn(p)}{dx}$$

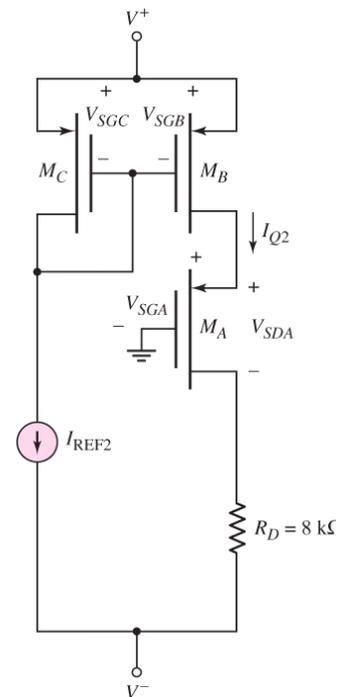
4.

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30% Design the circuit in Figure. The DC values are to be $I_{DQ} = 6 \text{ mA}$, $V_{GSQ} = 2.8 \text{ V}$, and $V_{DSQ} = 10 \text{ V}$. The $g_m = 2.2 \text{ mA/V}$. Let $R_L = 1 \text{ k}\Omega$, and $A_v = -1$, and $R_{in} = 100 \text{ k}\Omega$. Find R_1 , R_2 , R_S , R_D , K_n and V_{TN} .

5. 30% In Figure, all transistors have parameters $V_{TP} = -0.4 \text{ V}$ and $k'_p = 0.05 \text{ mA/V}^2$. The bias source are $V^+ = 5 \text{ V}$ and $V^- = -5 \text{ V}$. The currents are to be $I_{Q2} = 0.2 \text{ mA}$ and $I_{REF2} = 0.125 \text{ mA}$. For M_B , we require $V_{SDB}(\text{sat}) = 0.8 \text{ V}$, and for M_A , we require $V_{SDA} = 4 \text{ V}$. Transistor M_A and M_B are matched. (a) Find the W/L ratios of the transistors. (b) Find the value of R_D .



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